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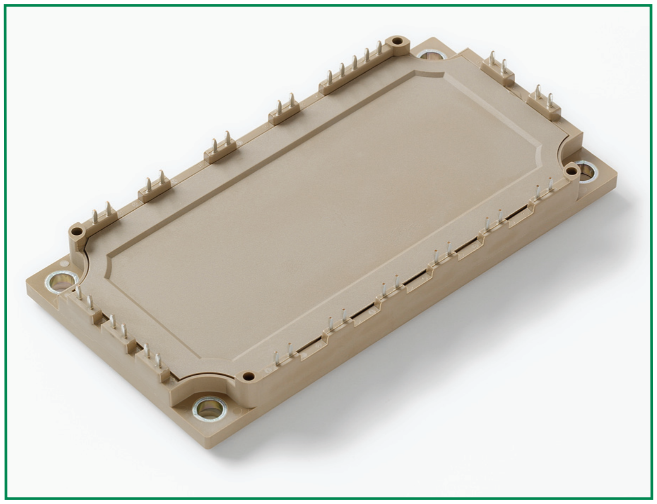
Power Module
1200V 75A IGBT Module

MG1275W-XBN2MM

RoHS



Features

- High level of integration—only one power semiconductor module required for the whole drive
- Low saturation voltage and positive temperature coefficient
- Fast switching and short tail current
- Free wheeling diodes with fast and soft reverse recovery
- Industry standard package with insulated copper base plate and soldering pins for PCB mounting
- Temperature sense included

Applications

- AC motor control
- Motion/servo control
- Inverter and power supplies

Module Characteristics (T_J = 25°C, unless otherwise specified)

Symbol	Parameters	Test Conditions	Min	Typ	Max	Unit
$T_{J\ max)}$	Max. Junction Temperature				150	°C
$T_{J\ op}$	Operating Temperature		-40		125	°C
T_{stg}	Storage Temperature		-40		125	°C
V_{isol}	Insulation Test Voltage	AC, t=1min		3000		V
CTI	Comparative Tracking Index		250			
M_d	Mounting Torque	Recommended (M5)	2.5		5	N·m
Weight				300		g

Absolute Maximum Ratings (T_J = 25°C, unless otherwise specified)

Symbol	Parameters	Test Conditions	Values	Unit
IGBT				
V_{CES}	Collector - Emitter Voltage	T_J=25°C	1200	V
V_{GES}	Gate - Emitter Voltage		±20	V
I_C	DC Collector Current	T_C=25°C	105	A
		T_C=80°C	75	A
I_{CM}	Repetitive Peak Collector Current	t_p=1ms	150	A
P_{tot}	Power Dissipation Per IGBT		348	W
Diode				
V_{RRM}	Repetitive Reverse Voltage	T_J=25°C	1200	V
$I_{F(AV)}$	Average Forward Current	T_C=25°C	105	A
		T_C=80°C	75	A
I_{FRM}	Repetitive Peak Forward Current	t_p=1ms	150	A
I^2t		T_J =125°C, t=10ms, V_R=0V	1150	A^2s

Revised:12/04/14

Electrical and Thermal Specifications (T_J = 25°C, unless otherwise specified)

Symbol	Parameters	Test Conditions		Min	Typ	Max	Unit
IGBT							
$V_{GE(th)}$	Gate - Emitter Threshold Voltage	$V_{CE}=V_{GE}$, I_C=3.0mA		5.0	5.8	6.5	V
$V_{CE(sat)}$	Collector - Emitter Saturation Voltage	I_C=75A, V_{GE}=15V, T_J=25°C			1.7		V
		I_C=75A, V_{GE}=15V, T_J=125°C			1.9		V
I_{CES}	Collector Leakage Current	V_{CE}=1200V, V_{GE}=0V, T_J=25°C				1	mA
		V_{CE}=1200V, V_{GE}=0V, T_J=125°C				10	mA
I_{GES}	Gate Leakage Current	V_{CE}=0V, V_{GE}=±15V, T_J=125°C		-400		400	nA
R_{Gint}	Integrated Gate Resistor				10		Ω
Q_{ge}	Gate Charge	V_{CE}=600V, I_C=75A , V_{GE}=±15V			0.7		μC
C_{ies}	Input Capacitance	V_{CE}=25V, V_{GE}=0V, f =1MHz			5.3		nF
C_{RES}	Reverse Transfer Capacitance				0.2		nF
$t_{d(on)}$	Turn - on Delay Time	V_{CC}=600V I_C=75A R_G =4.7Ω V_{GE}=±15V Inductive Load	T_J=25°C		260		ns
			T_J=125°C		290		ns
t_r	Rise Time		T_J=25°C		30		ns
			T_J=125°C		50		ns
$t_{d(off)}$	Turn - off Delay Time		T_J=25°C		420		ns
			T_J=125°C		520		ns
t_f	Fall Time		T_J=25°C		70		ns
			T_J=125°C		90		ns
E_{on}	Turn - on Energy		T_J=25°C		6.6		mJ
			T_J=125°C		9.4		mJ
E_{off}	Turn - off Energy		T_J=25°C		6.8		mJ
			T_J=125°C		8.0		mJ
I_{SC}	Short Circuit Current	t_{psc}≤10μS , V_{GE}=15V; T_J=125°C , V_{CC}=900V			300		A
R_{thJC}	Junction-to-Case Thermal Resistance (Per IGBT)					0.36	K/W
Diode							
V_F	Forward Voltage	I_F=75A, V_{GE}=0V, T_J =25°C			1.65		V
		I_F=75A, V_{GE}=0V, T_J =125°C			1.65		V
t_{RR}	Reverse Recovery Time	I_F=75A, V_R=600V di_F/dt=2000A/μs T_J=125°C			300		ns
I_{RRM}	Max. Reverse Recovery Current				85		A
E_{rec}	Reverse Recovery Energy				6.5		mJ
R_{thJCD}	Junction-to-Case Thermal Resistance (Per Diode)					0.6	K/W

Diode-Rectifier Absolute Maximum Ratings (T_J = 25°C, unless otherwise specified)

Symbol	Parameters	Test Conditions	Values	Unit
V_{RRM}	Repetitive Reverse Voltage	T_J=25°C	1600	V
$I_{F(AV)}$	Average Forward Current	T_C=80°C	75	A
I_{FRM}	Non-Repetitive Surge Forward Current	T_J=45°C, t=10ms, 50Hz	450	A
		T_J=45°C, t=8.3ms, 60Hz	400	
I^2t		T_J=45°C, t=10ms, 50Hz	1012	A^2s
		T_J=45°C, t=8.3ms, 60Hz	800	

Diode-Rectifier Electrical and Thermal Specifications (T_J = 25°C, unless otherwise specified)

Symbol	Parameters	Test Conditions	Min	Typ	Max	Unit
V_F	Forward Voltage	I_F=75A, T_J =25°C		1.25		V
		I_F=75A, T_J =125°C		1.15		V
I_R	Reverse Leakage Current	V_R=1600V, T_J =25°C			50	µA
		V_R=1600V, T_J =125°C			1	mA
R_{thJCD}	Junction-to-Case Thermal Resistance (Per Diode)				0.66	K/W

Brake-Chopper Absolute Maximum Ratings (T_J = 25°C, unless otherwise specified)

Symbol	Parameters	Test Conditions	Values	Unit
IGBT				
V_{CES}	Collector - Emitter Voltage	T_J=25°C	1200	V
V_{GES}	Gate - Emitter Voltage		±20	V
I_C	DC Collector Current	T_C=25°C	55	A
		T_C=80°C	40	A
I_{CM}	Repetitive Peak Collector Current	t_p=1ms	80	A
P_{tot}	Power Dissipation Per IGBT		195	W
Diode				
V_{RRM}	Repetitive Reverse Voltage	T_J=25°C	1200	V
$I_{F(AV)}$	Average Forward Current	T_C=25°C	35	A
		T_C=80°C	25	A
I_{FRM}	Repetitive Peak Forward Current	t_p=1ms	50	A
I^2t		T_J =125°C, t=10ms, V_R=0V	200	A^2s

Brake-Chopper Electrical and Thermal Characteristics (T_J = 25°C, unless otherwise specified)

Symbol	Parameters	Test Conditions		Min	Typ	Max	Unit
IGBT							
$V_{GE(th)}$	Gate - Emitter Threshold Voltage	$V_{CE}=V_{GE}$, I_C=1.5mA		5.0	5.8	6.5	V
$V_{CE(sat)}$	Collector - Emitter Saturation Voltage	I_C=40A, V_{GE}=15V, T_J=25°C			1.8		V
		I_C=40A, V_{GE}=15V, T_J=125°C			2.05		V
I_{CES}	Collector Leakage Current	V_{CE}=1200V, V_{GE}=0V, T_J=25°C				0.25	µA
		V_{CE}=1200V, V_{GE}=0V, T_J=125°C				2	mA
I_{GES}	Gate Leakage Current	V_{CE}=0V, V_{GE}=±15V, T_J=125°C		-400		400	nA
R_{Gint}	Integrated Gate Resistor				6		Ω
Q_{ge}	Gate Charge	V_{CE}=600V, I_C=40A , V_{GE}=±15V			0.33		µC
C_{ies}	Input Capacitance	V_{CE}=25V, V_{GE}=0V, f =1MHz			2.5		nF
C_{RES}	Reverse Transfer Capacitance				0.11		nF
$t_{d(on)}$	Turn - on Delay Time	V_{CC}=600V I_C=40A R_G =27Ω V_{GE}=±15V Inductive Load	T_J =25°C		90		ns
			T_J =125°C		90		ns
t_r	Rise Time		T_J =25°C		30		ns
			T_J =125°C		50		ns
$t_{d(off)}$	Turn - off Delay Time		T_J =25°C		420		ns
			T_J =125°C		520		ns
t_f	Fall Time		T_J =25°C		70		ns
			T_J =125°C		90		ns
E_{on}	Turn - on Energy		T_J =25°C		4.1		mJ
			T_J =125°C		6.0		mJ
E_{off}	Turn - off Energy		T_J =25°C		3.1		mJ
			T_J =125°C		3.6		mJ
I_{SC}	Short Circuit Current	t_{psc}≤10µS, V_{GE}=15V; T_J=125°C, V_{CC}=900V			160		A
R_{thJC}	Junction-to-Case Thermal Resistance (Per IGBT)					0.62	K/W
Diode							
V_F	Forward Voltage	I_F=25A , V_{GE}=0V, T_J =25°C			1.55		V
		I_F=25A , V_{GE}=0V, T_J =125°C			1.54		V
t_{RR}	Reverse Recovery Time	I_F=25A, V_R=600V di_F/dt=-400A/µs T_J=125°C			200		ns
I_{RRM}	Max. Reverse Recovery Current				20		A
E_{rec}	Reverse Recovery Energy				1.5		mJ
R_{thJCD}	Junction-to-Case Thermal Resistance (Per Diode)					1.22	K/W

NTC Characteristics (T_J = 25°C, unless otherwise specified)

Symbol	Parameters	Test Conditions	Min	Typ	Max	Unit
R_{25}	Resistance	T_c=25°C		5		KΩ
$B_{25/50}$				3375		K

Figure 1: Typical Output Characteristics for IGBT Inverter

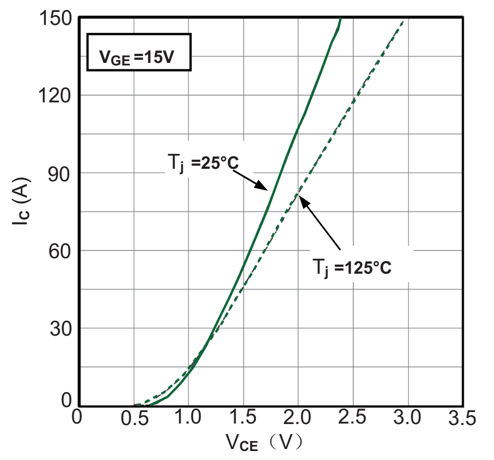


Figure 2: Typical Output Characteristics for IGBT Inverter

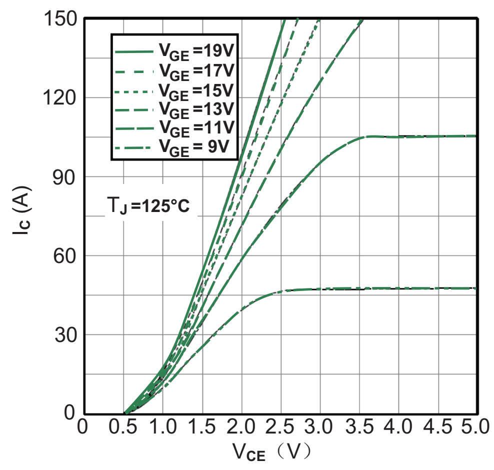


Figure 3: Typical Transfer Characteristics for IGBT Inverter

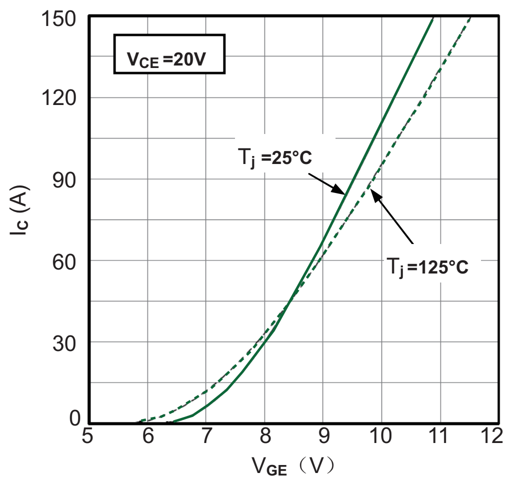


Figure 4: Switching Energy vs. Gate Resistor for IGBT Inverter

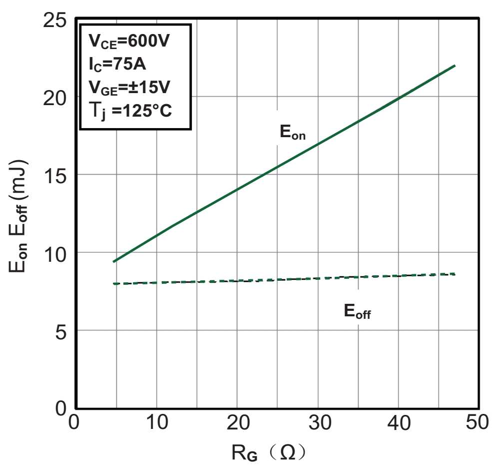


Figure 5: Switching Energy vs. Collector Current for IGBT Inverter

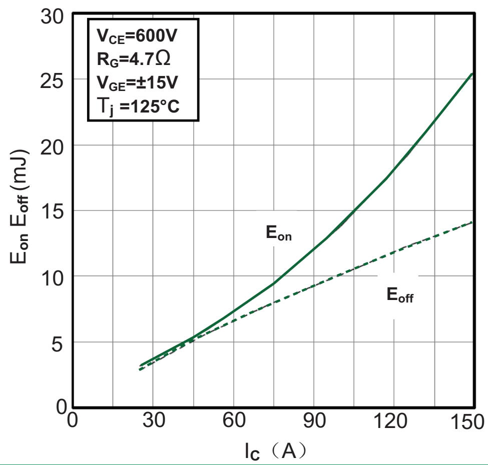


Figure 6: Reverse Biased Safe Operating Area for IGBT Inverter

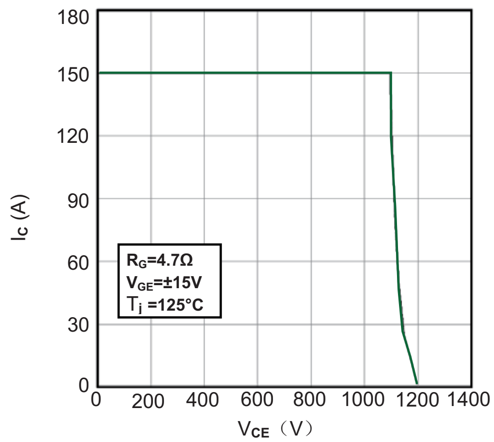


Figure 7: Diode Forward Characteristics for Diode Inverter

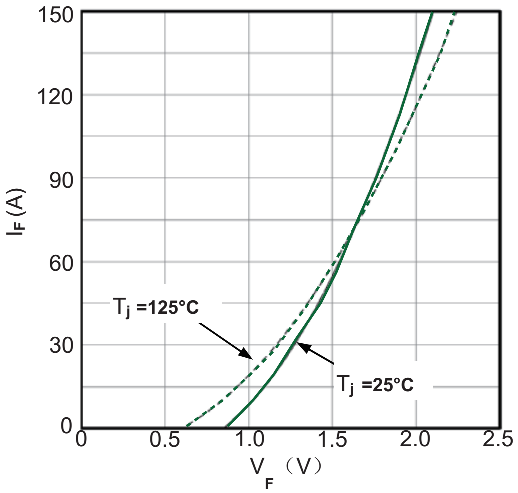


Figure 8: Switching Energy vs. Gate Resistort for Diode Inverter

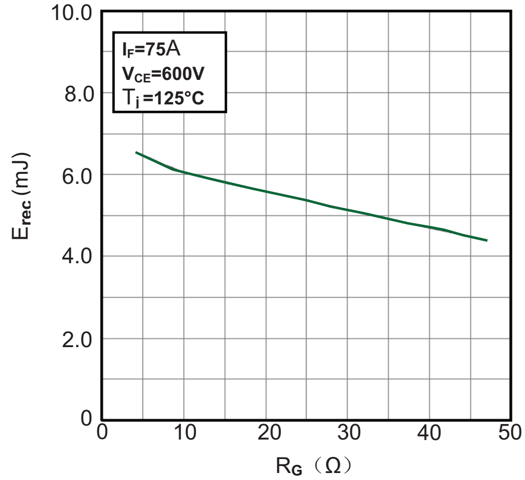


Figure 9: Switching Energy vs. Forward Current for Diode Inverter

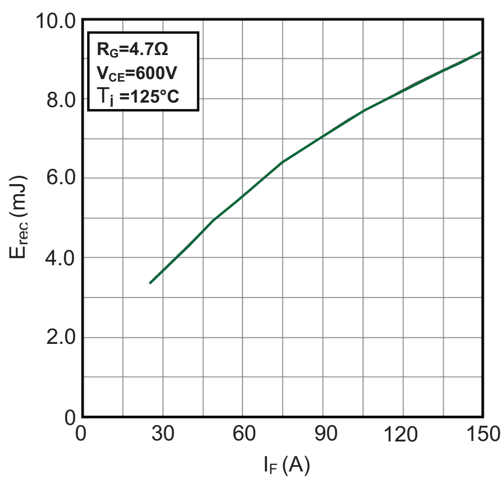


Figure 10: Transient Thermal Impedance of Diode and IGBT Inverter

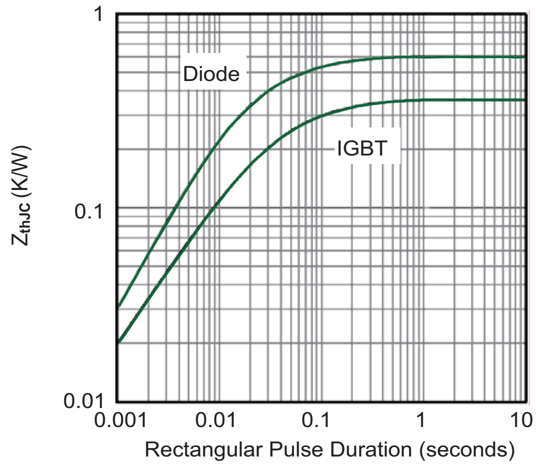


Figure 11: Diode Forward Characteristics for IGBT Inverter

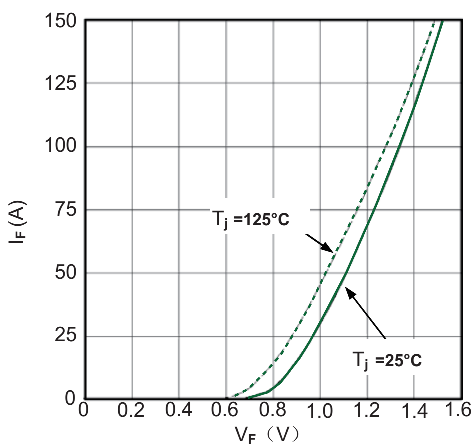


Figure 12: Typical Output Characteristics for IGBT Brake Chopper

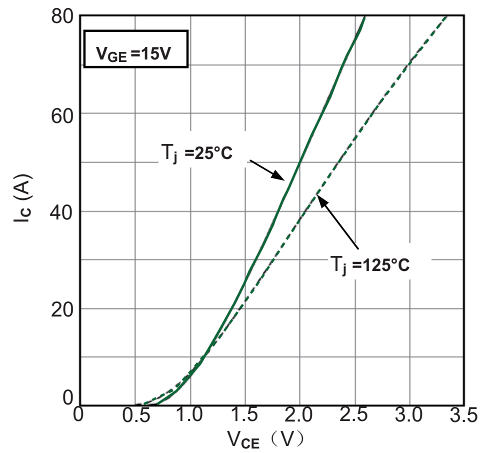


Figure 13: Diode Forward Characteristics for Diode Brake Chopper

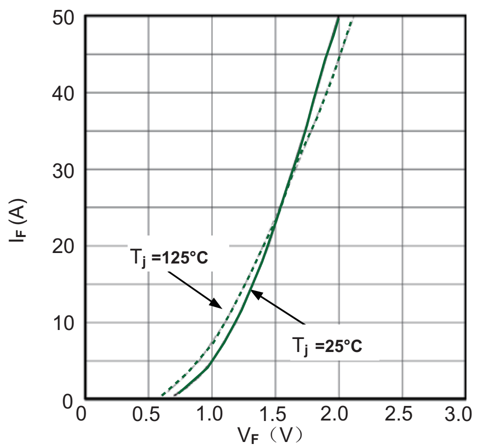
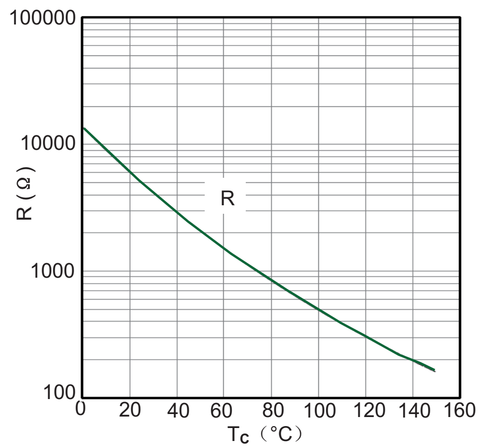
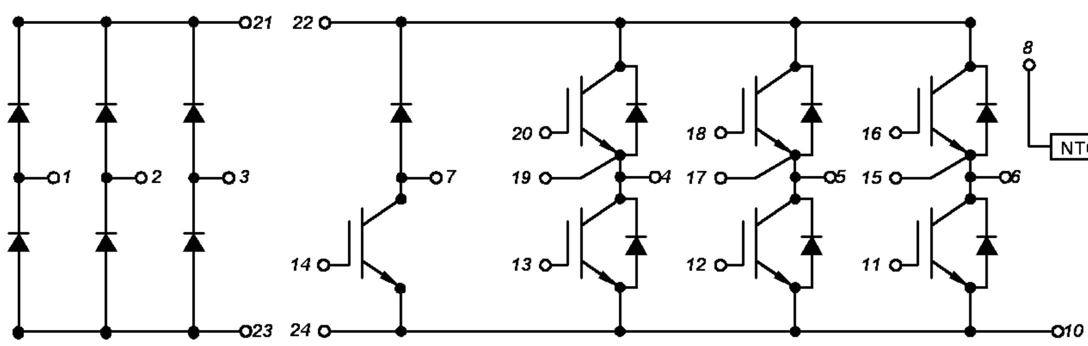


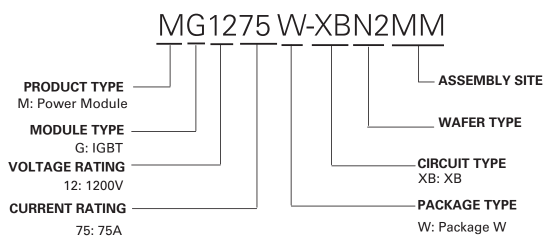
Figure 14: NTC Characteristics



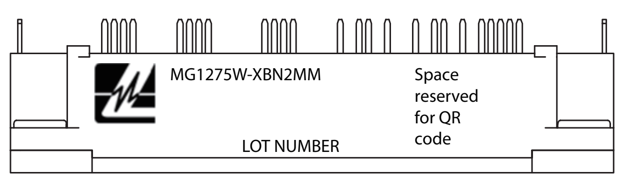
Circuit Diagram



Part Numbering System



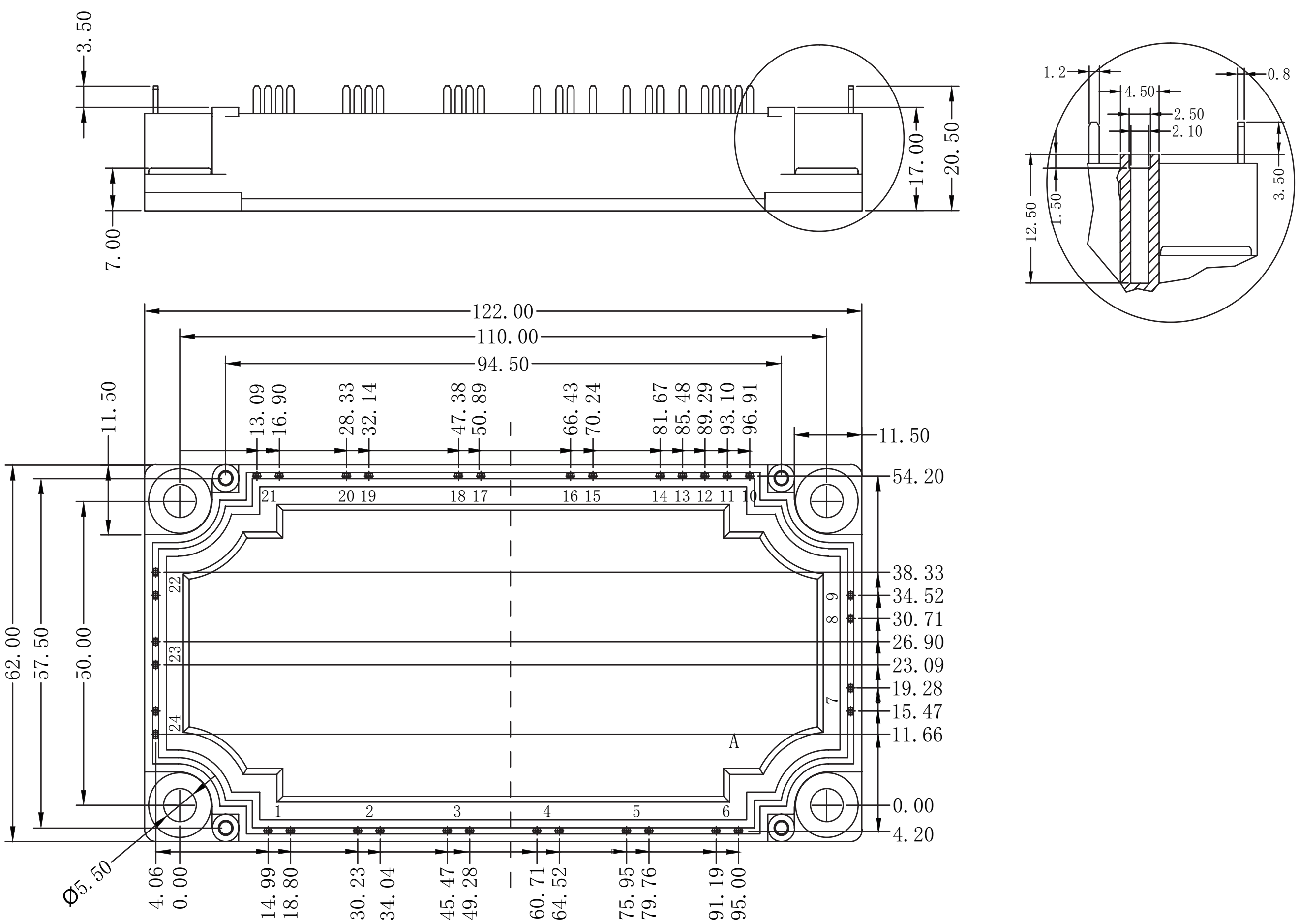
Part Marking System



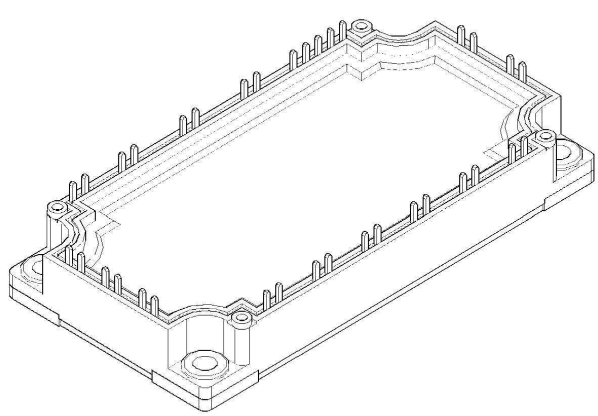
Packing Options

Part Number	Marking	Weight	Packing Mode	M.O.Q
MG1275W-XBN2MM	MG1275W-XBN2MM	300g	Bulk Pack	20

Dimensions-Package W



Dimensions (mm)



Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001
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Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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